

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Canceled)

2. (Currently Amended) A light emitting device comprising:

a thin film transistor on an insulating surface, wherein the thin film transistor contains a semiconductor layer and a gate electrode over the semiconductor layer, wherein the gate electrode contains a first conductive layer which has a tapered cross section and a second conductive layer which does not have a tapered cross section over the first conductive layer, and wherein a top surface of the first conductive layer is wider than a bottom surface of the second conductive layer;

an interlayer insulating film over the thin film transistor;

~~an anode having a first portion and a second portion over the interlayer insulating film, wherein the first portion has a leveling surface;~~

a wiring electrically connected to the thin film transistor and the anode;

a bank over the wiring and a portion of the anode;

an insulating film over ~~the leveling surface~~ of the anode and an upper surface of the bank;

an organic compound layer over the anode with the insulating film interposed therebetween; and

a cathode over the organic compound layer,

~~wherein the insulating film contains at least one of polyamide and acrylic.~~

3. (Currently Amended) A light emitting device comprising:

a thin film transistor on an insulating surface, wherein the thin film transistor contains a semiconductor layer and a gate electrode over the semiconductor layer, wherein the gate electrode contains a first conductive layer which has a tapered cross section and a second conductive layer which does not have a tapered cross section over the first conductive layer, and wherein a top surface of the first conductive layer is wider than a bottom surface of the second conductive layer;

an interlayer insulating film over the thin film transistor;

~~an anode having a first portion and a second portion over the interlayer insulating film, wherein the first portion has a leveling surface;~~

a wiring electrically connected to the thin film transistor and the anode;

a bank over the wiring and a portion of the anode;

an insulating film over ~~the leveling surface~~ of the anode and an upper surface of the bank;

an organic compound layer over the anode with the insulating film interposed therebetween; and

a cathode over the organic compound layer, and

~~wherein the insulating film contains at least one of polyamide and acrylic, and wherein the insulating film is at a film thickness of 1 to 5nm.~~

4. (Canceled)

5. (Currently Amended) A light emitting device comprising:

a thin film transistor on an insulating surface, wherein the thin film transistor contains a semiconductor layer and a gate electrode over the semiconductor layer, wherein the gate electrode contains a first conductive layer which has a tapered cross section and a second conductive layer which does not have a tapered cross section

over the first conductive layer, and wherein a top surface of the first conductive layer is wider than a bottom surface of the second conductive layer;

an interlayer insulating film over the thin film transistor;

~~an anode having a first portion and a second portion over the interlayer insulating film, wherein the first portion has a leveling surface;~~

a wiring electrically connected to the thin film transistor and the anode;

a bank over the wiring and a portion of the anode;

~~an insulating film over the leveling surface of the anode and an upper surface of the bank;~~

an organic compound layer over the anode with the insulating film interposed therebetween; and

a cathode over the organic compound layer, and

~~wherein the insulating film contains at least one of polyamide and acrylic, and wherein the anode is formed from indium tin oxide.~~

6. (Currently Amended) A light emitting device comprising:

a thin film transistor on an insulating surface, wherein the thin film transistor contains a semiconductor layer and a gate electrode over the semiconductor layer, wherein the gate electrode contains a first conductive layer which has a tapered cross section and a second conductive layer which does not have a tapered cross section over the first conductive layer, and wherein a top surface of the first conductive layer is wider than a bottom surface of the second conductive layer;

an interlayer insulating film over the thin film transistor;

~~an anode having a first portion and a second portion over the interlayer insulating film, wherein the first portion has a leveling surface;~~

a wiring electrically connected to the thin film transistor and the anode;

a bank over the wiring and a portion of the anode;

an insulating film over ~~the leveling surface of~~ the anode and an upper surface of the bank;

an organic compound layer over the anode with the insulating film interposed therebetween; and

a cathode over the organic compound layer,

~~wherein the insulating film contains at least one of polyamide and acrylic,~~

wherein the insulating film is at a film thickness of 1 to 5nm, and

wherein the anode is formed from indium tin oxide.

7.-12. (Canceled)

13. (Original) A device according to claim 2, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

14. (Original) A device according to claim 2, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

15. (Original) A device according to claim 2, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

16. (Original) A device according to claim 2,

wherein the bank is processed by a plasma; and

wherein the bank comprises a hardened film including at least an element selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen fluoride, and noble gas.

17. (Withdrawn) A device according to claim 2,

wherein a second insulating film is formed over the interlayer insulating film; and wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

18. (Original) A device according to claim 2,  
wherein the light emitting device is in combination with an electric device; and  
wherein the electric device is one selected from the group consisting of a display,  
a digital still camera, a notebook type personal computer, a mobile computer, an image  
reproduction apparatus including a recording medium, a goggle type display, a video  
camera and a mobile phone.

19. (Original) A device according to claim 3, wherein an average surface  
roughness (Ra) of the anode is in a range of 0.9 nm or less.

20. (Original) A device according to claim 3, wherein an average surface  
roughness (Ra) of the anode is in a range of 0.85 nm or less.

21. (Original) A device according to claim 3, wherein the interlayer insulating  
film comprises at least one selected from the group consisting of a silicon oxide film, a  
silicon nitride oxide film and a silicon oxide nitride film.

22. (Original) A device according to claim 3,  
wherein the bank is processed by a plasma; and  
wherein the bank comprises a hardened film including at least an element  
selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen  
fluoride, and noble gas.

23. (Withdrawn) A device according to claim 3,

wherein a second insulating film is formed over the interlayer insulating film; and wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

24. (Original) A device according to claim 3,  
wherein the light emitting device is in combination with an electric device; and  
wherein the electric device is one selected from the group consisting of a display,  
a digital still camera, a notebook type personal computer, a mobile computer, an image  
reproduction apparatus including a recording medium, a goggle type display, a video  
camera and a mobile phone.

25.-30. (Canceled)

31. (Original) A device according to claim 5, wherein an average surface roughness (Ra) of the anode is in a range of 0.9 nm or less.

32. (Original) A device according to claim 5, wherein an average surface roughness (Ra) of the anode is in a range of 0.85 nm or less.

33. (Original) A device according to claim 5, wherein the interlayer insulating film comprises at least one selected from the group consisting of a silicon oxide film, a silicon nitride oxide film and a silicon oxide nitride film.

34. (Original) A device according to claim 5,  
wherein the bank is processed by a plasma; and  
wherein the bank comprises a hardened film including at least an element  
selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen  
fluoride, and noble gas.

35. (Withdrawn) A device according to claim 5,  
wherein a second insulating film is formed over the interlayer insulating film; and  
wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.

36. (Original) A device according to claim 5,  
wherein the light emitting device is in combination with an electric device; and  
wherein the electric device is one selected from the group consisting of a display,  
a digital still camera, a notebook type personal computer, a mobile computer, an image  
reproduction apparatus including a recording medium, a goggle type display, a video  
camera and a mobile phone.

37. (Original) A device according to claim 6, wherein an average surface  
roughness (Ra) of the anode is in a range of 0.9 nm or less.

38. (Original) A device according to claim 6, wherein an average surface  
roughness (Ra) of the anode is in a range of 0.85 nm or less.

39. (Original) A device according to claim 6, wherein the interlayer insulating  
film comprises at least one selected from the group consisting of a silicon oxide film, a  
silicon nitride oxide film and a silicon oxide nitride film.

40. (Original) A device according to claim 6,  
wherein the bank is processed by a plasma; and  
wherein the bank comprises a hardened film including at least an element  
selected from the group consisting of hydrogen, nitrogen, halocarbon, hydrogen  
fluoride, and noble gas.

41. (Withdrawn) A device according to claim 6,  
wherein a second insulating film is formed over the interlayer insulating film; and  
wherein the second insulating film comprises at least one selected from the group consisting of a silicon nitride film and a diamond like carbon film.
42. (Original) A device according to claim 6,  
wherein the light emitting device is in combination with an electric device; and  
wherein the electric device is one selected from the group consisting of a display,  
a digital still camera, a notebook type personal computer, a mobile computer, an image  
reproduction apparatus including a recording medium, a goggle type display, a video  
camera and a mobile phone.
43. (Canceled)
44. (Previously Presented) A device according to claim 2,  
wherein the bank is formed from a resin insulating film.
45. (Previously Presented) A device according to claim 3,  
wherein the bank is formed from a resin insulating film.
46. (Previously Presented) A device according to claim 5,  
wherein the bank is formed from a resin insulating film.
47. (Previously Presented) A device according to claim 6,  
wherein the bank is formed from a resin insulating film.
48. (Canceled)

49. (Previously Presented) A device according to claim 2,  
wherein the leveling surface of the anode is formed by a wiping process using a  
porous material.
50. (Previously Presented) A device according to claim 3,  
wherein the leveling surface of the anode is formed by a wiping process using a  
porous material.
51. (Previously Presented) A device according to claim 5,  
wherein the leveling surface of the anode is formed by a wiping process using a  
porous material.
52. (Previously Presented) A device according to claim 6,  
wherein the leveling surface of the anode is formed by a wiping process using a  
porous material.
53. (New) A device according to claim 2, wherein the insulating film contains at  
least one of polyimide, polyamide and polyimide amide.
54. (New) A device according to claim 3, wherein the insulating film contains at  
least one of polyimide, polyamide and polyimide amide.
55. (New) A device according to claim 5, wherein the insulating film contains at  
least one of polyimide, polyamide and polyimide amide.
56. (New) A device according to claim 6, wherein the insulating film contains at  
least one of polyimide, polyamide and polyimide amide.